Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

H8550S

APPLICATIONS

Audio Frequency Amplifier.

ABSOLUTE MAXIMUM RATINGS（T_a=25℃）

T_{stg}——Storage Temperature…… -55~150℃

T_j——Juncttion Temperature……150℃

P_C——Collector Dissipation……625W

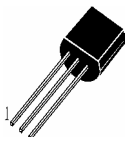
V_{CBO}——Collector-Base Voltage……-40V

V_{CEO}——Collector-Emitter Voltage……-20V

V_{EBO}——Emitter-Base Voltage……-5V

I_C——Collector Current……-500mA

TO-92



1－Emitter，E
2－Base，B
3－Collector，C

ELECTRICAL CHARACTERISTICS（T_a=25℃）

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
I_{CBO}	Collector Cut-off Current			-0.1	μA	V_{CB}=-25V, I_E=0
I_{EBO}	Emitter Cut-off Current			-0.1	μA	V_{EB}=-3V, I_C=0
H_{FE}（1）	DC Current Gain	85		500		V_{CE}=-1V, I_C=-50mA
H_{FE}（2）		40				V_{CE}=-1V, I_C=-500mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			-0.6	V	I_C=-500mA, I_B=-50mA
$V_{BE(sat)}$	Base- Emitter Saturation Voltage			-1.2	V	I_C=-500mA,I_B=-50mA
$V_{BE(on)}$	Base-Emitter On Voltage	-0.6		-0.73	V	V_{CE}=-1V, I_C=-10mA
BV_{CBO}	Collector-Base Breakdown Voltage	-40			V	I_C=-100μA，I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	-20			V	I_C=-2mA，I_B=0
BV_{EBO}	Emitter- Base Breakdown Voltage	-5			V	I_E=100μA，I_C=0

h_{FE} Classification

B	C	D	E
85—160	120—200	160—300	270—500

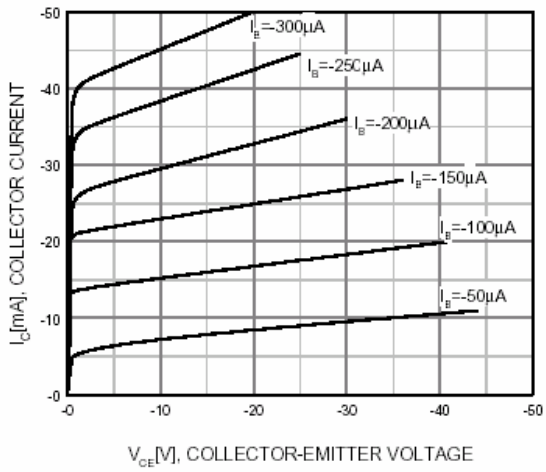


Figure 1. Static Characteristic

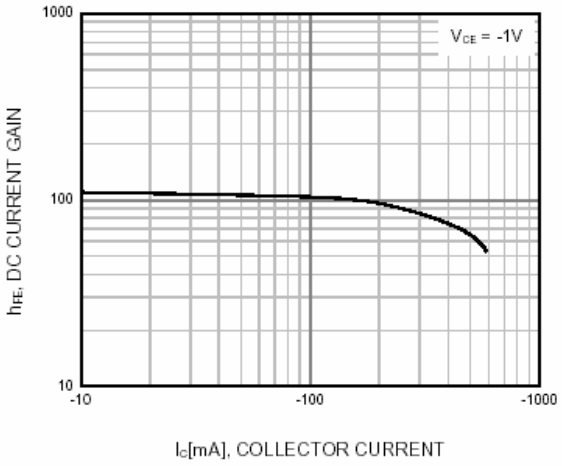


Figure 2. DC current Gain

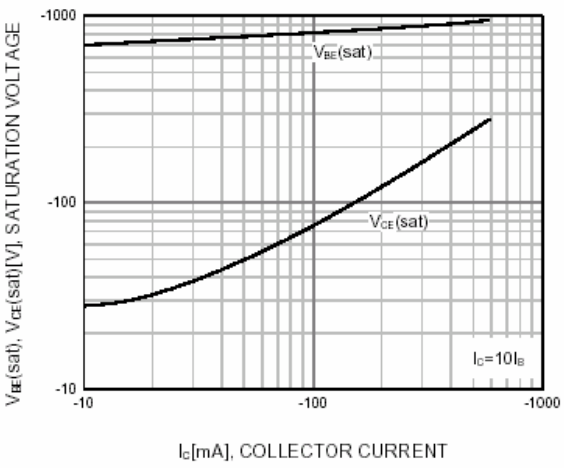


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

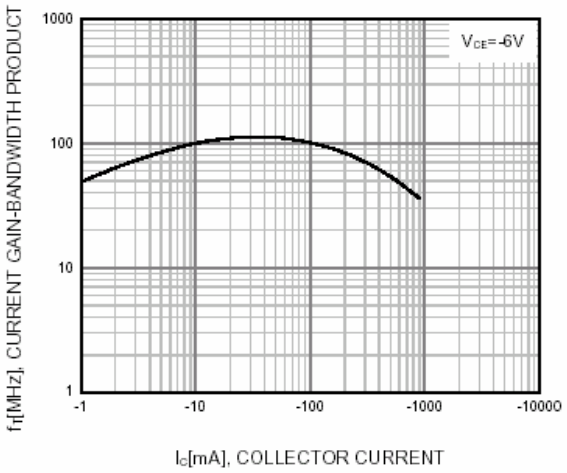


Figure 4. Current Gain Bandwidth Product